

isc Silicon NPN Darlington Power Transistor

2SD1510

DESCRIPTION

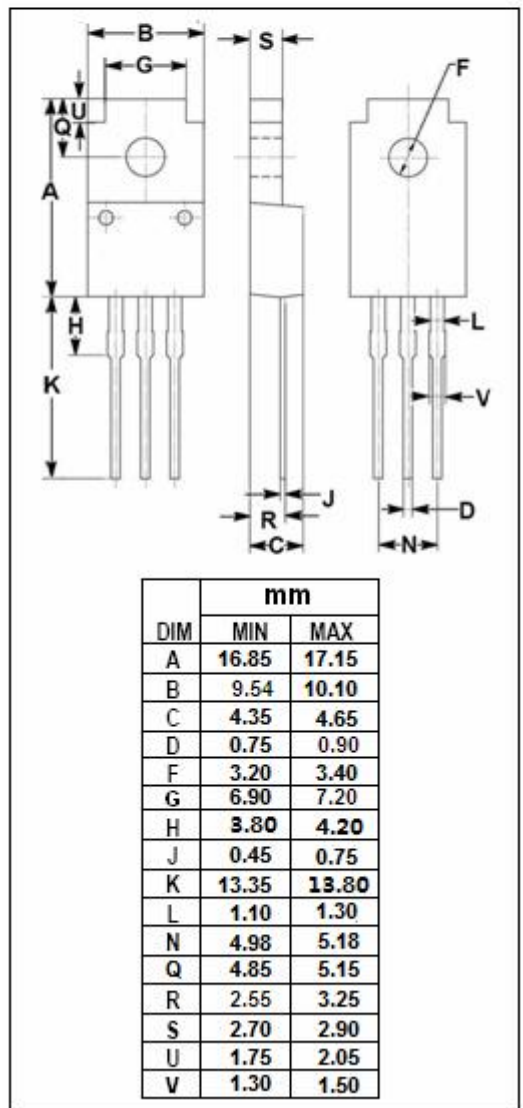
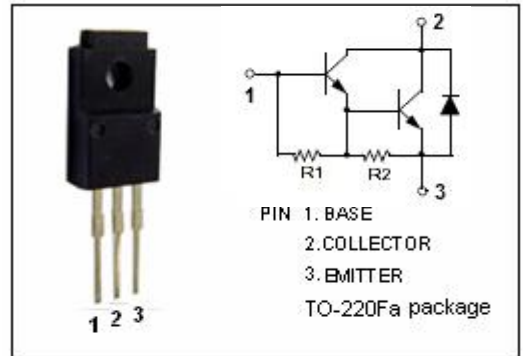
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 60V(\text{Min})$
- High DC Current Gain
: $h_{FE} = 1000(\text{Min}) @ I_C = 3A, V_{CE} = 3V$
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Power amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	4	A
I_{CM}	Collector Current-Peak	8	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	35	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon NPN Darlington Power Transistor**2SD1510****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 30mA ; I _B = 0	60			V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 3A; I _B = 12mA			2.0	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 20mA			4.0	V
V _{BE(on)}	Base -Emitter On Voltage	I _C = 3A ; V _{CE} = 3V			2.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 60V; I _E = 0			100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 6V; I _C = 0			2.0	mA
h _{FE-1}	DC Current Gain	I _C = 0.5A ; V _{CE} = 3V	1000			
h _{FE-2}	DC Current Gain	I _C = 3A ; V _{CE} = 3V	1000		10000	
f _T	Current-Gain—Bandwidth Product	I _C = 0.5A ; V _{CE} = 10V		20		MHz

h_{FE-2}Classifications

R	Q	P
1000-2500	2000-5000	4000-10000